Jin Nakam ura, Shin-ya Nasubida, Eiki Kabasawa, Hisashi Yamazaki, Nobuyoshi Yamada, Kazuhiko Kuroki Department of Applied Physics & Chemistry, The University of Electro-Communications, Chofu, Tokyo 182-8585, Japan

> M asam itsu W atanabe R IK EN /SP ring-8, K outo 1-1-1, M ikazuki, Sayo, H yogo 679-5148, Japan

Tam io O guchi Department of Quantum Matter, ADSM, Hiroshima University, Higashihiroshima-shi, Hiroshima 739-8530, Japan

Sergey Lee, A yako Yam am oto, Setsuko Tajin a, Superconductivity Research Laboratory, International Superconducting Technology Center, K oto, Tokyo 135-0062, Japan

> YujiUm eda, Shin M inakawa, NoriakiK im ura, HaruyoshiAoki, Center for Low Tem perature Science, Tohoku University, Sendai, M iyaqi 980-8578, Japan

ShigekiO tani Advanced M aterials Laboratory, N IM S, T sukuba, Ibaraki 305-0044, Japan

Shik Shin

The Institute for Solid State Physics (ISSP), The University of Tokyo, Kashiwa, Chiba 277-8581, Japan R IK EN /SP ring-8, K outo 1-1-1, M ikazuki, Sayo, H yogo 679-5148, Japan

> Thom as A.Callcott Department of Physics, University of Tennessee, Knoxville, TN 37996

D avid L.E derer D epartm ent of Physics, Tulane University, New Orleans, LA 70118

Jonathan D.Denlinger Advanced Light Source, Lawrence Berkeley National Laboratory, Berkeley, CA 94720

R upert C C . P erera C enter for X -ray O ptics, Law rence B erkeley N ational Laboratory, B erkeley, C A 94720 (A coepted to P R B : 2 July 2003)

The e ect of electron correlation (EC) on the electronic structure in MgB₂, AlB₂ and ZrB₂, is studied by examining the partial density of states (PDOS) of B-2p and p orbitals using the polarization dependence of x-ray emission and absorption spectra. The discrepancies between observed and calculated PDOSs cannot be attributed to EC e ects. The present results suggest that the EC e ect is less than the experimental error (0.2 eV), which indirectly supports a scenario that electron-phonon interaction plays an essential role in the occurrence of superconductivity.

74.70 Ad, 74.25 Jb, 78.70 Dm, 78.70 En

Since the discovery of superconductivity in M gB₂ with T_c of 39 K [1], a large number of researches from experimental [2{12] and theoretical [13{19] point of view have been performed on M gB₂ and on a series of isostructural diborides. M ost of these studies suggest that M gB₂ is a phonon-mediated BCS type superconductor. Bud'ko et al. reported a boron isotope e ect with = 0.26. [2] The tem perature dependence of ¹¹B-nuclear spin relaxation rate, 1=T₁, shows an exponential decay in the superconducting state revealing a tiny coherence peak just below

 T_c , which means that M gB₂ is an s-wave superconductor with a large band gap. [3] On the other hand, high resolution photoem ission spectroscopy and speci c heat measurement of M gB₂ suggest the two superconducting gaps. [4,5] The tunneling experiment also suggest that two gaps of about 2-3 and 7 m eV. [6] Recent Ram an study on the single crystalline M gB₂ assigned the two gaps to a large one (6.5 m eV) of the band and a sm all one (1.5 m eV) of the bands. [7] These results are in contradiction with a scenario that M gB₂ is a simple s-wave

superconductor. Theoretical band calculations [13,14], in the early stage, have suggested that the dimensionless electron-phonon coupling (EPC) constant 0.7, which can give a high T_c of 40 K if the Coulomb potential

is very small. On the other hand, two-band mechanism s based on inter-band electron-correlation (EC) have been proposed. [15{18] In these mechanisms, inter-band EC (and bands considered by Im ada, and bonding and antibonding -bands by Yam a ji) enhances T_c from a conventional BCS (EPC based) value, and the mechanism s have relationship with the experimental results that suggest the two superconducting gaps [47]. In order to understand the high $T_{\rm c}$ of M gB_2 , therefore, it is necessary to get information on the EC e ects in the superconducting M gB₂ and non-superconducting other diborides. The density of state gives in portant inform ation on the EC e ects. The partial density of states (PDOS) of boron have been m easured by x-ray absorption (XAS) and x-ray emission (XES) spectroscopy near B-K edge of polycrystalline M qB₂ and other A \mathbb{B}_2 -type compounds, in which the observed PDOS agrees well with the band calculations. [8{10] Furtherm ore, angle resolved photoemission spectroscopic (ARPES) [20] and de Haas van Alphen (dHvA) e ect [21] studies were perform ed on the single crystalline M gB₂ sam ple [22]. The ARPES spectra along the -K and -M directions show three dispersive curves that can be assigned to theoretically predicted and bands. However, som e predicted bands were not observed. In addition, a small parabolic-like band is observed around the point, which can not be explained by band calculations. Because this technique is quite surface sensitive, the results m ay not represent the bulkelectronic structure. On the other hand, dH vA technique is useful to probe the bulk-electronic structure. Yelland et al. reported that only three dHvA frequencies were resolved am ong four Ferm i surfaces predicted theoretically. The derived three dHvA frequencies and the large e ective m ass are, how ever, explained by precise band calculation, [23,24] the calculation insists that the bands near E_F should shift with decreasing number of holes near $E_{\,\rm F}$. They pointed out that the discrepancies between the experim ental results and the band calculations may be caused by EC e ects or beyond-LDA e ect. Furtherm ore, several authors have proposed a model based on a weak electron-phonon coupling [25] that is consistent with the optical conductivity and DC resistivity studies of c-axis oriented MgB₂ Im s [26]. Thus, it is necessary to investigate the signi cance of the EC e ects, which can play an important role on the appearance of high T_c in M gB₂. XAS and XES measurements of single crystalare quiet useful for this purpose because these techniques give PDOS which can re ect the existence of strong EC .XAS and XES of single crystalline A \mathbb{B}_2 and XAS of single crystalline M $g_x A \downarrow_x B_2$ were already perform ed, [11,12] in which a good agreem ent between the observation and the band calculation was reported. In this paper, we report a direct observation of PDOS of B-2p and 2p by polarization dependent XES and XAS

2

near B-K edge using single crystalline M gB₂, A B_2 and ZrB_2 sam ples. Comparing the observed PDOS with the rst principle band calculation results [27], we exam ine the signi cance of EC e ects in M gB.

The single crystalline M gB₂ sam ples were grown in BN container under high pressure. [22] A B₂ and ZrB₂ crystals were prepared by A - ux [11] and FZ m ethods [28], respectively. The XES m easurem ent was perform ed at BL-2C in KEK-PF, in which the energy of the incident photons is about 400 eV. The energy resolution of XES spectrom eter is about 0.2 eV. The XAS spectra were m easured at BL-8.0.1 of A dvanced Light Source (ALS) in LBNL by the partial uorescence yield (PFY) m ethod. The energy resolution of the incident photons is about 0.1 eV.PDOSs of each B-2p and 2p orbitals are derived from polarization dependence of XES and XAS spectra. [11]

Figure 1 shows the observed partial density of states (PDOS) of B-2p [Fig. 1(b)] and p states [Fig. 1(c)] from observed polarization-dependent XES and XAS spectra with the results of band calculation. Solid and dotted lines in Fig.1 are the results of the st principle band calculations (FLAPW method) by O guchi [27], which are convoluted by gaussian function with FW HM of the experim ental resolution. Solid and open circles (or squares) represent occupied and empty states of p (or p), respectively. It is clearly seen that the Ferm i energy E_F [A in Figs. 1(b) and (c)] measured from B-1s core level of M gB_2 is 186.4 eV, which agrees well with the previous reports. [9] In the Figs. 1 (b) and (c), the theoretical E_F value is set to the experimental E_F value, 186.4 eV.A sharp peak B in XES spectrum [Fig.1(b)] is observed at around E $E_F = 2:4 \text{ eV} \cdot 0 \text{ bserved PDOS}$ of p in XES spectrum steeply decreases at E_F and a considerable amount of PDOS just above E_F is observed in XAS spectrum. The p -PDOS near E_F disappears above 0.6 eV (C), and there is almost no p -PDOS in the energy region D (0.6 eV < E E_F < 3.6 eV). Figure 1 (c) show sXES (I) and XAS (2) of B-2p of M gB₂.0bserved PDOS of p shows a broad m etallic state except a large sharp peak G at 5.6 eV. The overall features of observed XAS near E_F and XES are well reproduced by the band calculation. However, in whole energy region, som e discrepancies are observed as follows. Observed peak B is lower than the theoretical prediction by 0.3 eV. The value of observed pseudo-gap is about 3 eV in contrast to the prediction of about 4 eV. Peaks, E_1 and E_2 in p -XAS and G in p -XAS, are not reproduced by the band calculation. Before going into detailed com parison between the theory and the experiment, let us show the results A \mathbb{B}_2 .

Figure 2 shows PDOS of A \mathbb{B}_2 with the same symbols of M gB₂ in Fig.1. The observed E_F is estimated to be 187.5 eV which agrees well with the previous report. [9,11] The value of E_F is slightly lower than the theoret-ical prediction by 0.6 eV, but the small shift is explained by the lack of A latom s by 0.07 from the stoichiom etric A \mathbb{B}_2 . [11] As in M gB₂, overall shapes of experimental

p - and p - PDOS are in good agreem ent with the band calculation results. Especially, in A B₂, it is found that a detailed shape of PDOS including a pseudo-gap in the empty state is in good agreem ent with the theoretical prediction within the experim ental resolution. This is in contrast with the case of M gB₂.

Figure 3 shows p () - and p ()-PDOS of ZrB derived from XES spectra. [29] In sharp contrast to the PDOS sofM gB₂ and A B₂, the p -PDOS of ZrB₂ shows clearly-resolved two-large peaks at about 184.3 eV and 185.4 eV, respectively. The p -PDOS also shows two peaks at about 183.0 eV and 184.3 eV. Both PDOSs decrease with increasing energy, but the sm all Ferm i edge is observed in both PDOSs. The E_F is estimated to be 188.1 eV. The solid and dotted lines are the theoretical ones with the experimental E_F value. As in M gB₂ and A B₂, even though the PDOS shapes are di erent, the observed PDOSs of ZrB₂ are well reproduced by the rst principle band calculation. The detailed com parison between observed PDOS and theoretical ones is as follows.

As mentioned before, overall shapes of the observed PDOSs of these compounds are roughly reproduced by the band calculations, but som e discrepancies are pointed out in $M gB_2$ and $A B_2$. A sharp peak B in $M gB_2$, which is due to van Hove singularity (VHS) of p band at M and L-points, slightly shifts from the theoretical prediction by about 0:3 eV . An energy, m easured from E $_{\rm F}$, of bonding p -top at -point [C in Fig. 1(b)] is about 0.6 eV in M gB₂ and 1:0 eV in A \mathbb{B}_2 , respectively. It agrees with the theoretical prediction in M gB_2 , and agrees with the prediction in $A \mathbb{B}_2$ assuming the E_F shifting. [11] However, in $M qB_2$, observed anti-bonding p PDOSs E_1 and E_2 are higher than the theoretical ones F_1 and F₂. This means the observed pseudo-gap located at region D is smaller than the theoretical prediction in M qB_2 by about 1 eV.On the other hand, in A \mathbb{B}_2 , one can see an excellent agreem ent between observed and theoretical PDOS around the pseudo-gap of about 3 eV. The values of observed pseudo-gap of both com pounds are the sam e (3 eV). In A \mathbb{B}_2 , there is no characteristic structure in PDOS above $E_F + 5 \text{ eV}$. Therefore, it seems that there is no discrepancy between experim ental and theoretical PDOS in A \mathbb{B}_2 compound even in the high energy region.

The large sharp peak G is due to p resonant state of the sample surface or of som e oxides of the surface. [8] And it does not appear in a polished-large single-crystal of A \mathbb{B}_2 . For A \mathbb{B}_2 single crystal, in order to remove the A - ux on the surface, the crystals were polished. [11] Therefore the uorescence spectrum will be free from the surface oxidation. But the size of M gB_2 single crystals is too sm all to rem ove surface oxides by polishing. Then the sm all am ount of oxides leads to the resonant peak G in MgB₂ spectrum. The present observation of PDOS of p band also agrees with the theoretical one except for the surface states m entioned above. The present results indicate that the experim ental PDO Ss are reproduced by the band calculation in the energy region of E < E_F+5 eV in both diborides.

O ne m ight consider that the discrepancy between experiment and the theory in the XAS regime of MgB₂ may be due to EC e ects that is not properly taken into account in LDA band calculations. However, the EC e ects generally tend to widen the gap, while in the present case, the experimental band gap is narrower than the theoretical one. Then, this discrepancy between the experiment and the theory may be attributed to the fact that the band calculation deals with the ground state of the system. A possible reason for the gap narrowing might be due to an excitonic e ect [30] that arises in the excited states of the XAS process, which is not taken into account in the band calculation.

In a previous paper [9], we insisted that a rigid band picture is valid for the relation between M gB $_2$ and A \mathbb{B}_2 . The present detailed PDOSs of both com pounds do not deny the rigid band picture, but suggest a sm all discrepancy between both compounds, i.e., anti-bonding p states is lower than the theoretical prediction in M qB_2 but that in $A \mathbb{B}_2$ is in agreement with the theoretical one. In ZrB₂, the observed p -PDOS structure is sim ilar to the theoretical PDOS of Zr-4d. [29] The high energy peak at 184.3 eV of p-PDOS is also sim ilar to the Zr-4dyz;zx PDOS, but the low energy PDOS at 183.0 eV is considered to be based on the covalent character of B-B bonding in basalplane. A sm entioned in the introductory part, there are two types of theoretical two-bands m odel based on electron-phonon [14] and inter-band EC m echanisms [15,18] in MgB₂ superconductivity. The present result indicates that the EC is smaller than the value of the present energy resolution (0.2 eV) in M gB₂, A B₂ and ZrB₂ compounds. The inter-band EC has a possibility to enhance the phonon-m ediated T_c . [15,18] If a sm all inter-band EC e ect that can not be detected in our experim ent enhances the high T_c, the present result does not contradict with these propositions.

To sum marize, in order to exam ine the electron correlation (EC) e ect in the diborides, we have perform ed direct m easurem ent of PDOS of B-2p in single-crystalline M gB₂, A B₂ and ZrB₂ using polarization-dependent XES and XAS measurements. Although there are some discrepancies between observed PDOSs and theoretical ones, the rst principle band calculation reproduces well the overall features of observed p - and p - PDOSs. In superconducting $M gB_2$, a considerable amounts of p hole state near the Ferm i energy is clearly observed. The pseudo-gap of p band is observed in $M gB_2$ and $A B_2$ com pounds in sharp contrast to the broad m etallic state of the B-2p bands. The observed gap values of about 3 eV are same in both compounds, which is smaller than the theoretically predicted value for M gB₂ and is consistent with it for $A \mathbb{B}_2$. Because the band calculation describes the ground state, it may be plausible that the calculation reproduces the experim ental PDOS only for $E < E_F + 5 \text{ eV}$ in both compounds. In ZrB₂, the observed PDOSs reproduced well by the calculation, suggest strong hybridization between B-2p and Zr-4d orbitals. The observed discrepancies are contrary to the

EC e ects. The present results suggest that the EC effect is less than the experim ental error (0.2 eV), which indirectly supports a scenario that electron-phonon interaction plays an essential role in the occurrence of superconductivity in M gB₂. How ever, a possibility of a sm all inter-band electron-correlation e ect which supports the phonon m ediated superconductivity, still rem ains.

JN. and SN. thank to Dr. Y. Kobayashi of RIKEN for the support with the synthesis of A \mathbb{B}_2 single crystals. K K. acknowledges Dr. J. Yam auchi of Toshiba Corporate R&D Center for valuable discussions. This work was supported by O ce of Basic Energy Science of the Department of Energy under contract Nos. DE-AC03-76SF00098 and W -7405-Eng-48, National Science Foundation (NSF) G rant No. DM R-9017996 to the University of Tennessee and a Grant-in-Aid No. 14540330 and No.13CE2002 (for COE Research) of the Ministry of Education, Culture, Sports, Science and Technology of Japan. This work was performed under the approval of the KEK-PF Advisory Committee (Proposal No. 2001U004). D.L.E. and T.A.C. also wish to acknowledge support from NSF G rant DM R-9801804.

FIG.1. The partial density of states (PDOS) of p and p of M gB₂. (a) The theoretical PDOS derived from FLAPW m ethod broadened with experim ental resolution. The solid and dotted lines are PDOS's of 2 p and p, respectively. (b) The experim ental PDOS of 2 p, occupied one (solid circle) and empty one (open circle). (c) The experim ental PDOS of p, occupied one (solid square) and empty one (open square).

FIG.2. The partial density of states (PDOS) of p and p of A \mathbb{B}_2 . (a) The theoretical PDOS derived from FLAPW m ethod broadened with experim ental resolution. The solid and dotted lines are PDOS'sof2 p and p, respectively. (b) The experim ental PDOS of2 p, occupied one (solid circle) and empty one (open circle). (c) The experim ental PDOS of p, occupied one (solid square) and empty one (open square).

FIG.3. The partial density of states (PDOS) of 2 p () and p () of ZrB₂. The solid and dotted lines are theoretical PDOSs of 2 p and p, respectively, which are broadened with experimental resolution.

- J.N agam atsu, N.N akagawa, T.M uranaka, Y.Zenitani and J.A kim itsu, Nature (London) 410, 63 (2001).
- [2] S.L. Bud'ko, G. Lapertot, C. Petrovic, C.E. Cunningham, N. Anderson, and P.C. Can eld, Phys. Rev. Lett. 86, 1877 (2001).
- [3] H K otegawa, K. Ishida, Y. K itaoka, T. M uranaka, and J. A kim itsu, Phys. Rev. Lett. 87, 127001 (2001).

- [4] S.T suda, T.Yokoya, T.K iss, Y.Takano, K.Togano, H. Kito, H.Ihara, and S.Shin, Phys. Rev. Lett. 87, 177006 (2001).
- [5] F.Bouquet, Y.W ang, R A.Fisher, D G.Hinks, J.D.Jorgensen, A.Junod, N E.Phillips, Europhys.Lett. 56, 856 (2001).
- [6] P. Szabo, P. Samuely, J. Kacmarcik, T. Klein, J. Marcus, D. Fruchart, S. Miraglia, C. Marcenat and A.G. M. Jansen, Phys. Rev. Lett. 87, 137005 (2001).
- [7] JW .Quilty, S.Lee, A.Yam am oto, and S.Tajim a, Phys. Rev. Lett. 88, 087001 (2002); JW .Quilty, S.Lee, S. Tajim a, and A.Yam am oto, Phys. Rev. Lett. 90, 207006 (2003).
- [8] T.A. Callcott, L. Lin, G.T. Woods, G.P. Zhang, J.R.Thompson, M. Paranthaman, D.L. Ederer, Phys. Rev. B 64, 132504 (2001).
- [9] J.Nakamura, N.Yamada, K.Kuroki, T.A. Callcott, D.L. Ederer, J.D. Denlinger and R.C. C. Perera, Phys. Rev. B 64, 174504 (2001).
- [10] E Z.Kurm aev, I.I.Lyakhovskaya, J.Kortus, A.Moewes, N.Miyata, M.Dem eter, M.Neumann, M.Yanagihara, M.Watanabe, T.Muranaka, J.Akimitsu, Phys. Rev. B 65, 134509 (2002).
- [11] J. Nakamura, M. W atanabe, T. Oguchi, S. Nasubida, E. Kabasawa, N. Yamada, K. Kuroki, H. Yamazaki, S. Shin, Y. Umeda, S. M inakawa, N. K imura and H. Aoki, J. Phys. Soc. Jpn. 71, 408 (2002).
- [12] S. Schuppler, E. Pellegrin, N. Nucker, T. M izokawa, M. Merz, D A. Arena, J.D vorak, Y J. Idzerda, D.-J. Huang, C.-F. Cheng, K.-P. Bohnen, R. Heid, P. Schweiss, Th. Wolf, cond-m at/0205230 (unpublished).
- [13] J.Kortus, I.I.Mazin, K D.Belashchenko, V P.Antropov, L L.Boyer, Phys. Rev. Lett. 86, 4656 (2001).
- [14] JM . An and W E. Pickett, Phys. Rev. Lett. 86, 4366 (2001).
- [15] M . Im ada, J. Phys. Soc. Jpn. 70, 1218 (2001).
- [16] A.Y. Liu, I.I.M azin, and J.K ortus, Phys. Rev. Lett. 87 087005 (2001).
- [17] S.V. Shulga, S.-L.D rechsler, H.E schrig, H.R osner, and W E.Pickett, cond-m at/0103154 (unpublished).
- [18] K.Yamaji, J.Phys.Soc.Jpn.70, 1476 (2001).
- [19] H J. Choi, D. Roundy, H. Sun, M L. Cohen, and S.G. Louie, Nature 418, 758 (2002).
- [20] H. Uchiyama, K M. Shen, S. Lee, A. Dam ascelli, D H. Lu, D L. Feng, Z.-X. Shen and S. Tajima, Phys. Rev. Lett. 88, 157002 (2002).
- [21] E A.Yelland, J.R. Cooper, A. Carrington, N.E. Hussey, P.J.M. eeson, S.Lee, A.Yam am oto, and S.Tajima, Phys. Rev.Lett. 88, 217002 (2002).
- [22] S.Lee, H.Mori, T.Masui, Y.Eltsev, A.Yamamoto, and S.Tajima, J.Phys.Soc.Jpn.70, 2255 (2001).
- [23] I.I. M azin and J. Kortus, Phys. Rev. B 65 180510R (2002).
- [24] H.Rosner, JM.An, W E.Pickett, and S.L.D rechsler, Phys.Rev.B 66 024521 (2002).
- [25] F.Marsiglio, Phys. Rev. Lett. 87, 247001 (2001).
- [26] J.J.Tu, G.L.Carr, V.Perebeinos, C.C.Homes, M.Strongin, P.B.Allen, W.N.Kang, E.M.Choi, H.J.Kim, Sung-Ik Lee, Phys. Rev. Lett. 87 277001 (2001).
- [27] T.Oguchi, J.Phys.Soc.Jpn.71, 1495 (2002).

- [28] S. O htani and Y. Ishizawa, J. Crystal G row th 165, 319 (1996).
- [29] M .W atanabe, unpublished.
- [30] Two points should be mentioned here. First, although the excitonic e ect is a Coulom bic e ect, it is not essentially an EC e ect. Namely, the excitonic shift of the energy can essentially be evaluated within a mean eld scheme if we take into account the excited states of the system. Secondly, one m ay consider that excitonic e ects m ay not be so large in metallic systems, where the screening of the Coulom b potential is prominent. If that is indeed the case, a clearcut reason for the discrepancy between theory and the experiment remains to be an open question. However, since EC e ects generally tend to widen the gap, we believe our scenario that the EC e ects is not so large in M gB₂ remains unchanged in any case.

This figure "Fig1.png" is available in "png" format from:

http://arxiv.org/ps/cond-mat/0307376v1

This figure "Fig2.png" is available in "png" format from:

http://arxiv.org/ps/cond-mat/0307376v1

This figure "Fig3.png" is available in "png" format from:

http://arxiv.org/ps/cond-mat/0307376v1